N-Channel 80-V (D-S) MOSFET

Key Features:

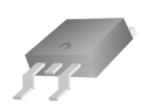
- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

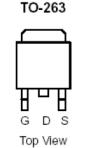
Typical	l Applica	ations:
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- · White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

PRODUCT SUMMARY				
V _{DS} (V)	$r_{DS(on)}(m\Omega)$	I⊳(A)		
80	11 @ V _{GS} = 10V	90 ^a		
60	13 @ $V_{GS} = 4.5V$	90		







ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)							
Parameter			Limit	Units			
Drain-Source Voltage			80	V			
Gate-Source Voltage			±20	V			
Continuous Drain Current a	T _C =25°C	I_D	90	Α			
Pulsed Drain Current ^b			390				
Continuous Source Current (Diode Conduction) ^a			110	Α			
Power Dissipation ^a	T _C =25°C	P_{D}	300	W			
Operating Junction and Storage Temperature Range		T_J , T_{stg}	-55 to 150	°C			

THERMAL RESISTANCE RATINGS			
Parameter	Symbol	Maximum	Units
Maximum Junction-to-Ambient ^a	$R_{\theta JA}$	62.5	°C/W
Maximum Junction-to-Case	$R_{\theta JC}$	1	C/VV

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Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Electrical Characteristics

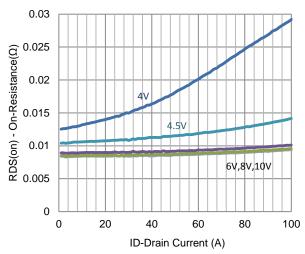
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250 \text{ uA}$	1			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current	lana	$V_{DS} = 64 \text{ V}, V_{GS} = 0 \text{ V}$			1	uA	
Zero Gate Voltage Brain Gurrent	I _{DSS}	$V_{DS} = 64 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			25	u/\	
On-State Drain Current	$I_{D(on)}$	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	120			Α	
Drain-Source On-Resistance	r	$V_{GS} = 10 \text{ V}, I_{D} = 45 \text{ A}$			11	mΩ	
Dialii-30dice Oil-Resistance	r _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 44 \text{ A}$			13	11152	
Forward Transconductance	g _{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 20 \text{ A}$		30		S	
Diode Forward Voltage	V_{SD}	$I_{S} = 55 \text{ A}, V_{GS} = 0 \text{ V}$		0.92		V	
		Dynamic					
Total Gate Charge	Q_g	$V_{DS} = 40 \text{ V}, V_{GS} = 4.5 \text{ V},$		60		nC	
Gate-Source Charge	Q_{gs}	$V_{DS} = 40 \text{ V}, V_{GS} = 4.3 \text{ V},$ $I_{D} = 20 \text{ A}$		12			
Gate-Drain Charge	Q_gd	10 - 20 A		37			
Turn-On Delay Time	t _{d(on)}	$V_{DS} = 40 \text{ V}, R_{L} = 2 \Omega,$		19			
Rise Time	t _r	$V_{DS} = 40 \text{ V}, N_L - 2 \Omega,$ $I_D = 20 \text{ A},$		45		ns	
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$		178			
Fall Time	t _f	VGEN = 10 V, NGEN = 0 12		62			
Input Capacitance	C _{iss}			5052			
Output Capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		471		pF	
Reverse Transfer Capacitance	C_{rss}			466			

Notes

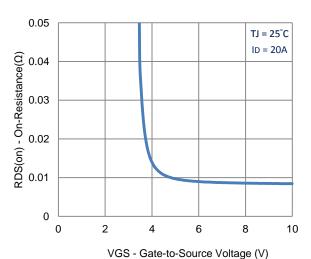
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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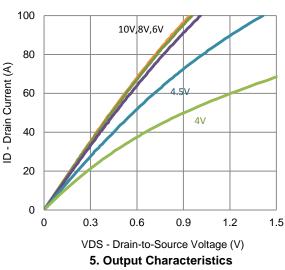
Typical Electrical Characteristics

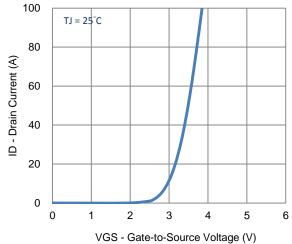


1. On-Resistance vs. Drain Current

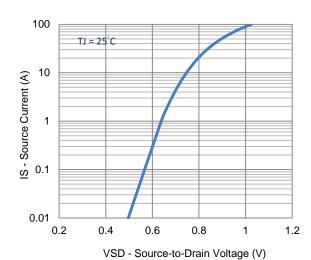


3. On-Resistance vs. Gate-to-Source Voltage

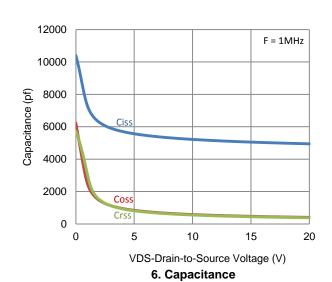




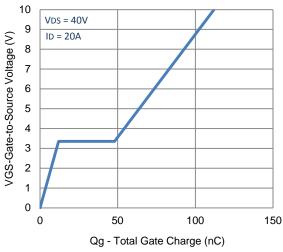
2. Transfer Characteristics



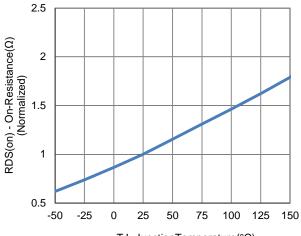
4. Drain-to-Source Forward Voltage



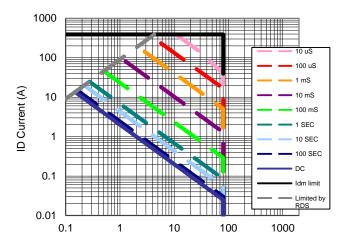
Typical Electrical Characteristics





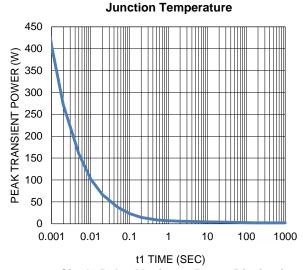


TJ -JunctionTemperature(°C)
8. Normalized On-Resistance Vs

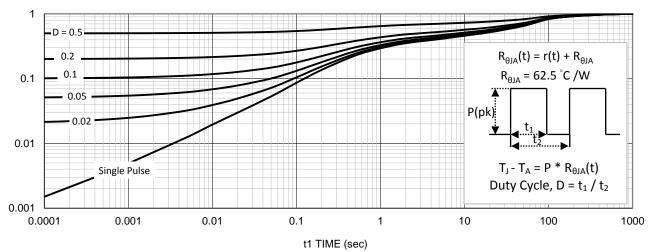


VDS Drain to Source Voltage (V)

9. Safe Operating Area

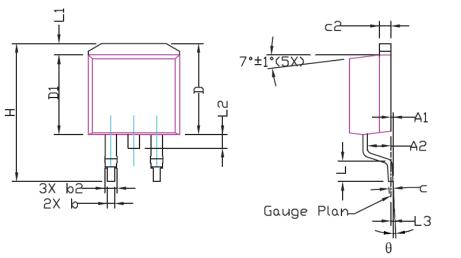


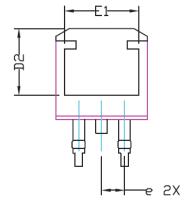
10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

Package Information





CVAADEI	DIMENSIONAL REQMTS			INCHES REQMTS			
SYMBOL	MIN	NDM	MAX	MIN	NDM	MAX	
Α	4,30	4.57	4,72	0.169	0.180	0.186	
A1	0		0,25	0		0.010	
A2	2,47	2.57	2,67	0.097	0.101	0.105	
b	0.69	0,813	0.94	0.027	0.032	0.037	
b2	1.17	1.27	1.45	0.046	0.050	0.057	
C	0.48	0,50	0.60	0.019	0.020	0.024	
c2	1.17	1.27	1.37	0.046	0.050	0,054	
D	9,80	10.05	10,30	0.386	0,396	0.406	
D1	8,64	8.78	9,65	0.340	0,346	0,380	
D2	7.12	7,37	7,62	0.280	0,290	0,300	
E	9,70	10.15	10.54	0.382	0.400	0.415	
E1	8,00	8,20	8,40	0.315	0,323	0.331	
е	2.	54 BSC	,	0.	100 BSC	,	
H	14,99	15.24	15,49	0.590	0.600	0.610	
L	1,78	2.29	2.79	0.070	0.090	0.110	
L1	1.02	1.27	1.52	0.040	0.050	0,060	
L2			1.75			0.069	
L3		0,254			0.010		
θ	0.		8•	0.		8.	